

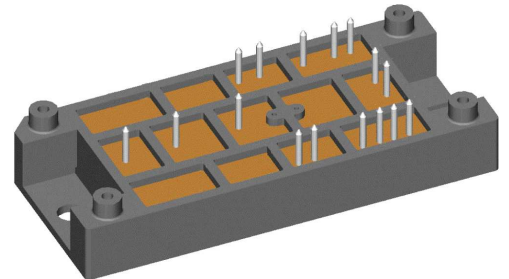
# Standard Rectifier Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 180 \text{ A}$	$I_{C25} = 250 \text{ A}$
$I_{FSM} = 1100 \text{ A}$	$V_{CE(sat)} = 1.7 \text{ V}$

## 3~ Rectifier Bridge + Brake Unit + NTC

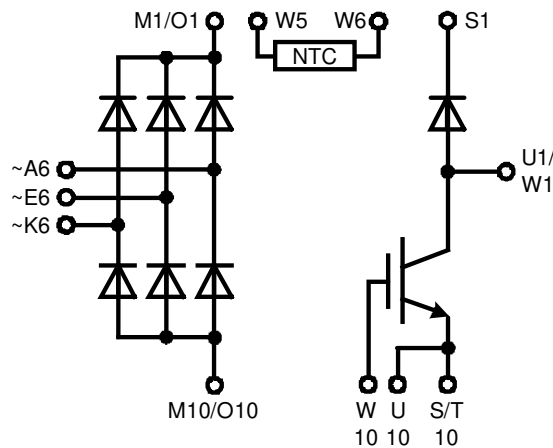
Part number

**VUB160-16NOXT**



Backside: isolated

 E72873



### Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- X2PT - 2nd generation Xtreme light Punch Through
- Rugged X2PT design results in:
  - short circuit rated for 10  $\mu\text{sec}$ .
  - very low gate charge
  - low EMI
  - square RBSOA @ 2x  $I_c$
- Thin wafer technology combined with X2PT design results in a competitive low  $V_{CE(sat)}$  and low thermal resistance

### Applications:

- 3~ Rectifier with brake unit for drive inverters

### Package: V2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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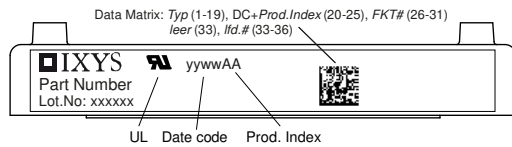
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1700	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1600	V
$I_R$	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		100	$\mu\text{A}$
		$V_R = 1600$ V		$T_{VJ} = 125^\circ\text{C}$		2	mA
$V_F$	forward voltage drop	$I_F = 60$ A		$T_{VJ} = 25^\circ\text{C}$		1.16	V
		$I_F = 180$ A				1.55	V
		$I_F = 60$ A		$T_{VJ} = 125^\circ\text{C}$		1.09	V
		$I_F = 180$ A				1.59	V
$I_{DAV}$	bridge output current	$T_C = 90^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		180	A
$V_{FO}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^\circ\text{C}$		0.81	V
$r_F$	slope resistance					4.4	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.6	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.2		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		205	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.10	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.19	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		935	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		1.01	kA
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		6.05	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		5.89	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		4.37	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		4.25	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		37	pF



Brake IGBT + Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}C$			250	A	
$I_{C80}$		$T_C = 80^{\circ}C$			175	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}C$			695	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 150\text{ A}; V_{GE} = 15\text{ V}$			1.7	V	
					1.9	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 6\text{ mA}; V_{GE} = V_{CE}$	6	6.8	7.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$			0.1	mA	
					0.1	mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 150\text{ A}$		510		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 150\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 1.2\ \Omega$	$T_{VJ} = 125^{\circ}C$		220	ns	
$t_r$	current rise time				100	ns	
$t_{d(off)}$	turn-off delay time				400	ns	
$t_f$	current fall time				220	ns	
$E_{on}$	turn-on energy per pulse				21.5	mJ	
$E_{off}$	turn-off energy per pulse				17	mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 1.2\ \Omega$					
$I_{CM}$		$V_{CEK} = 1200\text{ V}$			450	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEK} = 1200\text{ V}$					
$t_{SC}$	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15$	$T_{VJ} = 125^{\circ}C$		10	$\mu s$	
$I_{SC}$	short circuit current	$R_G = 1.2\ \Omega$ ; non-repetitive		650		A	
$R_{thJC}$	thermal resistance junction to case				0.16	K/W	
$R_{thCH}$	thermal resistance case to heatsink				0.10	K/W	
<b>Brake Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage				1200	V	
$I_{F25}$	forward current		$T_C = 25^{\circ}C$		48	A	
$I_{F80}$			$T_C = 80^{\circ}C$		32	A	
$V_F$	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}C$		2.75	V	
			$T_{VJ} = 125^{\circ}C$	1.60		V	
$I_R$	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}C$		0.25	mA	
			$T_{VJ} = 125^{\circ}C$		1	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{ V}$ $-di_f/dt = 900\text{ A}/\mu s$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}C$		6	$\mu C$	
$I_{RM}$	max. reverse recovery current				50	A	
$t_{rr}$	reverse recovery time				350	ns	
$E_{rec}$	reverse recovery energy				2	mJ	
$R_{thJC}$	thermal resistance junction to case				0.9	K/W	
$R_{thCH}$	thermal resistance case to heatsink				0.3	K/W	



Package V2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			100	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				76		g
$M_D$	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
$V_{ISOL}$	isolation voltage	t = 1 second 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUB160-16NOXT	VUB160-16NOXT	Box	6	521692

Similar Part	Package	Voltage class
VUB160-16NOX	V2-Pack	1600

**Temperature Sensor NTC**

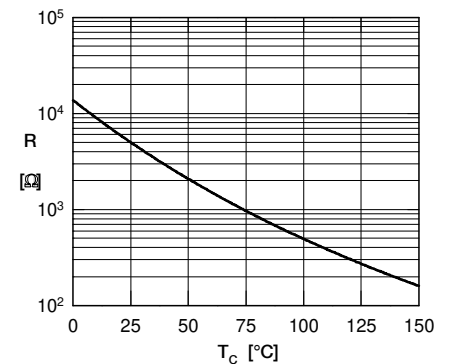
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$R_{25}$	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	k $\Omega$
$B_{25/50}$	temperature coefficient			3375		K

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^\circ\text{C}$

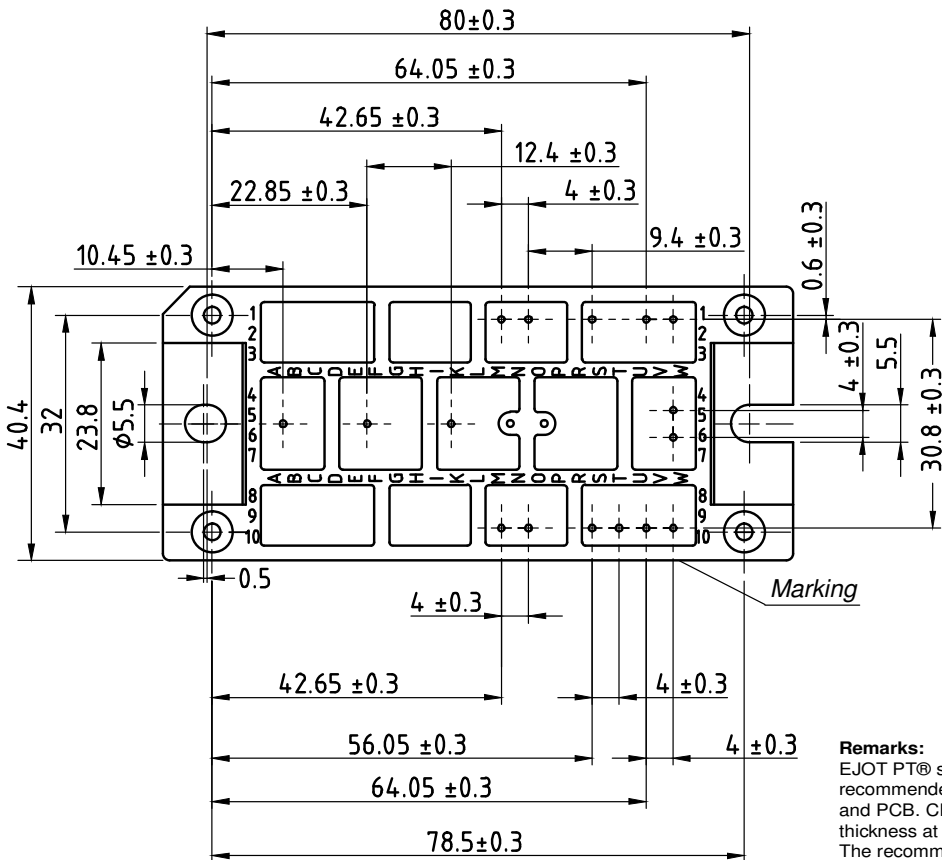
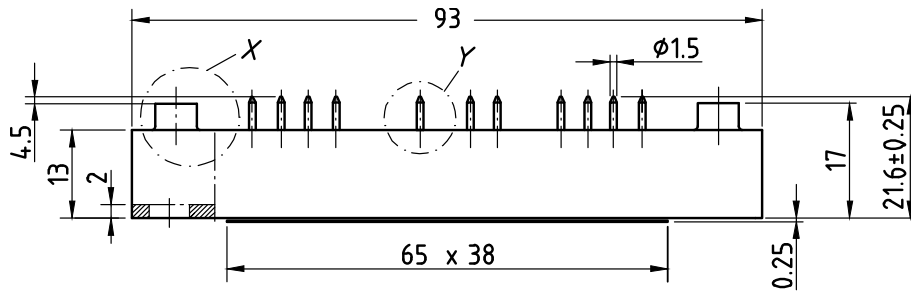
	Rectifier	Brake IGBT +	Brake Diode	
$V_{0\max}$	threshold voltage	0.81	1.1	1.31 V
$R_{0\max}$	slope resistance *	3.2	13.8	8 m $\Omega$



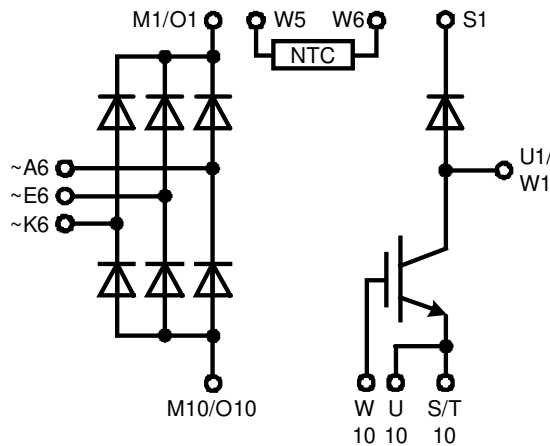
Typ. NTC resistance vs. temperature



**Outlines V2-Pack**



**Remarks:**  
EJOT PT® self-tapping screws of the dimension K25 are recommended for the mechanical connection between module and PCB. Choose the right length according to your board thickness at a maximum depth of 6 mm of the module holes. <sup>L</sup>  
The recommended mounting torque is 1.5 Nm.



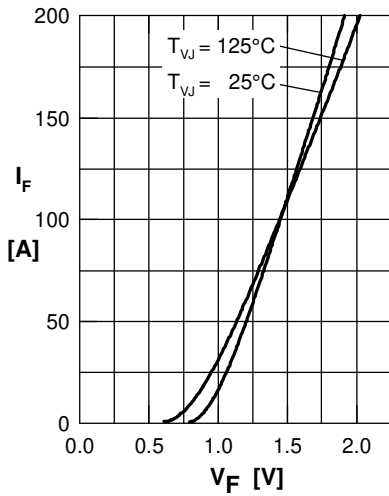
**Rectifier**


Fig. 1 Forward current vs. voltage drop per diode

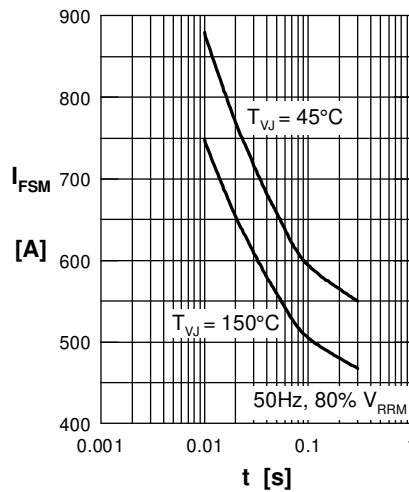


Fig. 2 Surge overload current vs. time per diode

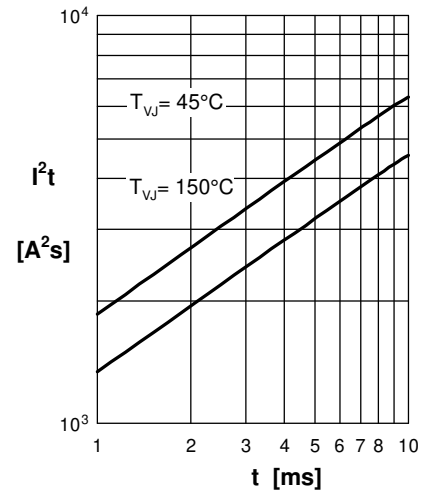
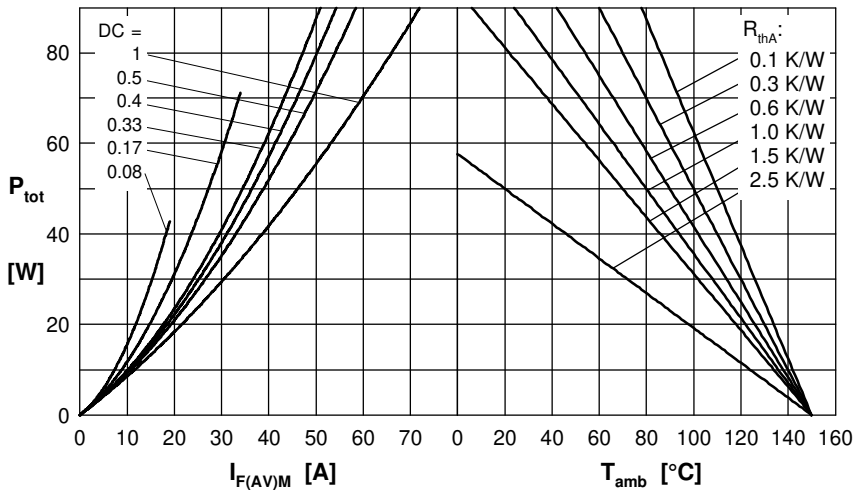

 Fig. 3  $I^2t$  vs. time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

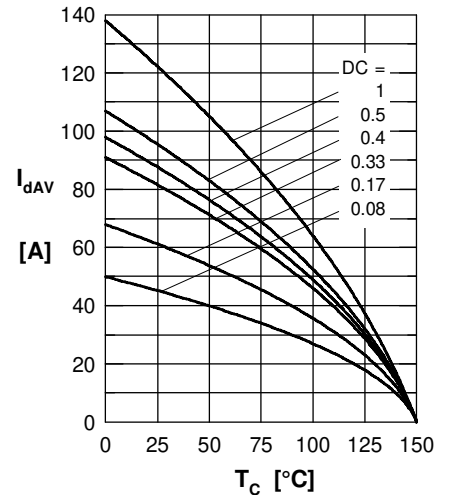


Fig. 5 Max. forward current vs. case temperature per diode

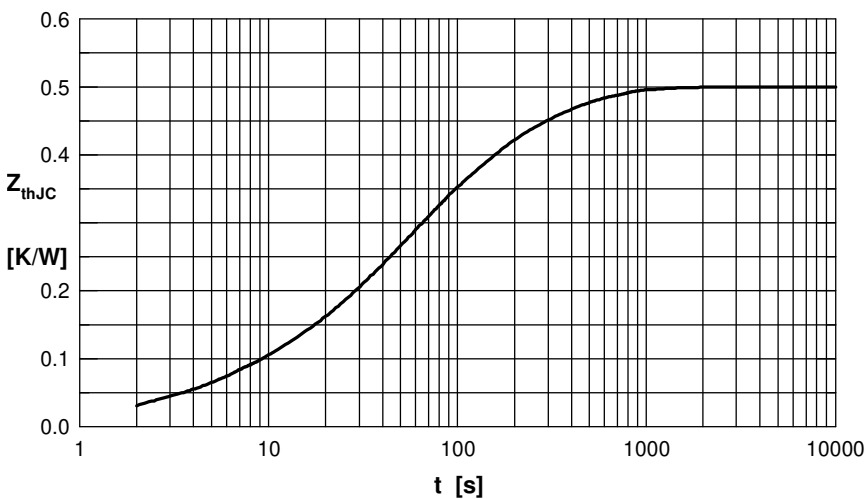


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for  $Z_{thJC}$  calculation:

i	$R_{th}$ (K/W)	$t_i$ (s)
1	0.040	0.004
2	0.003	0.010
3	0.140	0.030
4	0.120	0.300
5	0.197	0.080

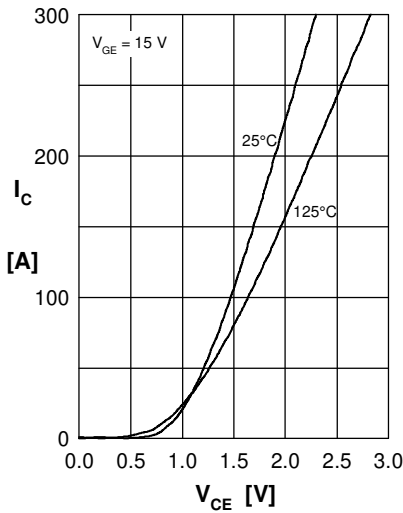
**Brake IGBT + Diode**


Fig.1 Output characteristics IGBT

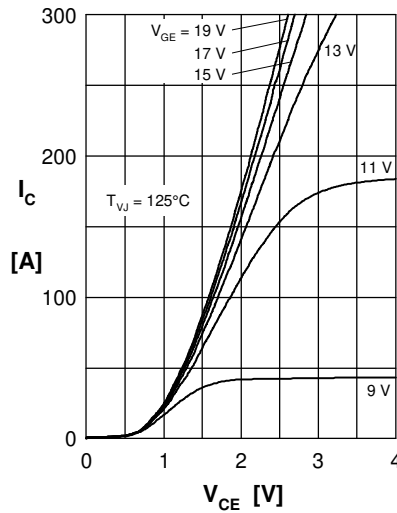


Fig.2 Typ. output characteristics IGBT

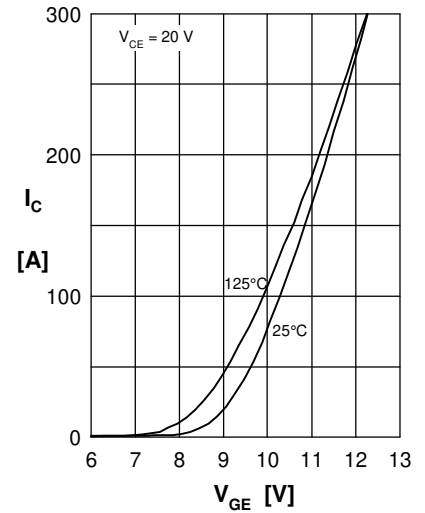


Fig.3 Typ. transfer charact. IGBT

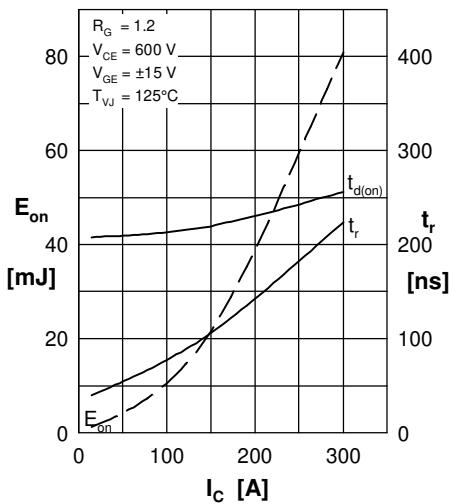


Fig.4 Typ. turn-on energy &amp; switch. times vs. collector current

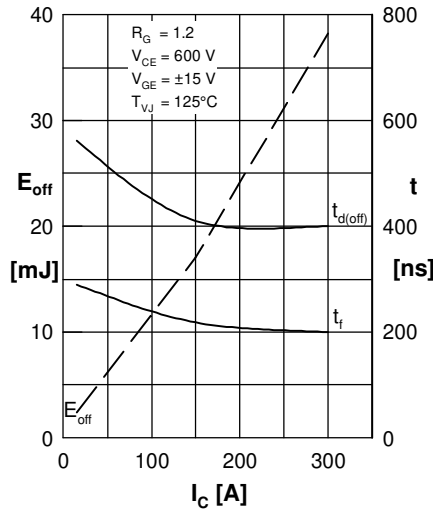


Fig.5 Typ. turn-off energy &amp; switch. times vs. collector current

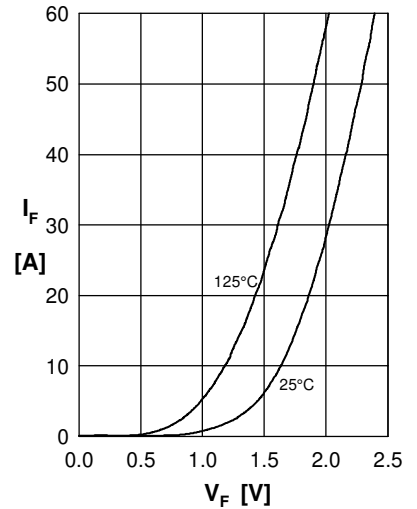


Fig.6 Typ. forward characteristics Diode

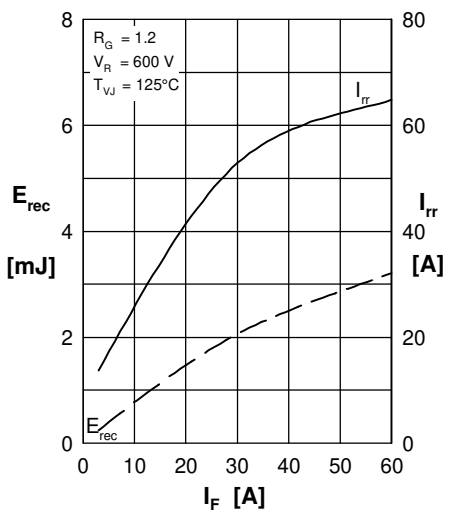


Fig.7 Typ. reverse recovery characteristics Diode

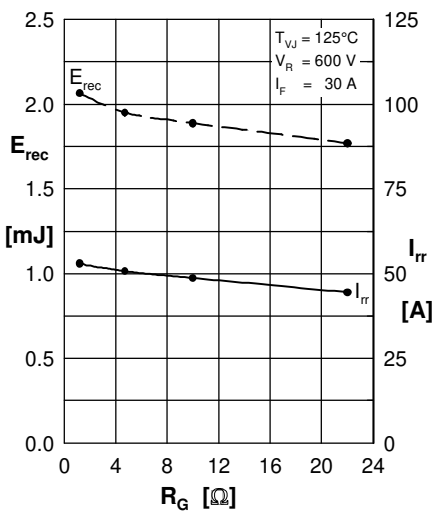


Fig.8 Typ. reverse recovery characteristics Diode

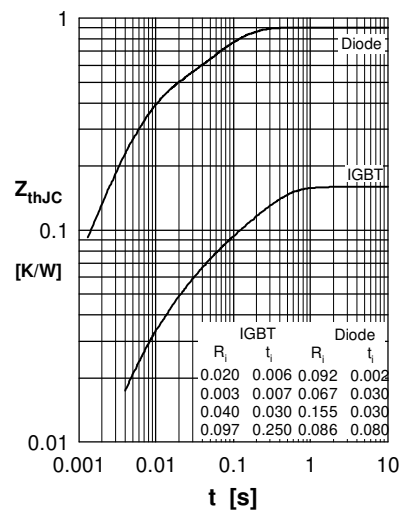


Fig.9 Transient thermal resistance junction to case

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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